

WHAT IS CLAIMED IS:

1. A method for contact opening definition for active element electrical connections, said method comprising the steps of:
 - forming a layer of BPSG on a surface of an integrated circuit; and
 - forming a transparent layer of nitride UV above the layer of BPSG.
2. The method according to claim 1, further comprising the step of:
 - after the step of forming a transparent layer of nitride UV, forming two overlapped layers of BARC and resist on the surface of the integrated circuit.
3. The method according to claim 2, further comprising the step of:
 - after the step of forming two overlapped layers of BARC and resist, chemically etching the integrated circuit so as to form contact openings.
4. The method according to claim 3, further comprising the step of:
 - before the step of forming a layer of BPSG, forming a USG oxide layer on the surface of the integrated circuit, the USG oxide layer having a thickness of between about 500Å and 2500Å.
5. The method according to claim 1, further comprising the step of:
 - before the step of forming a layer of BPSG, forming a USG oxide layer on the surface of the integrated circuit, the USG oxide layer having a thickness of between about 500Å and 2500Å.
6. The method according to claim 1, wherein in the step of forming the transparent layer of nitride UV, the transparent layer of nitride UV is formed by deposition using an HDP process.

7. The method according to claim 6, wherein the transparent layer of nitride UV has a thickness of between about 100Å and 500Å.

8. The method according to claim 1, wherein in the step of forming the transparent layer of nitride UV, the transparent layer of nitride UV is formed by deposition using a CVD process.

9. The method according to claim 8, wherein the transparent layer of nitride UV has a thickness of between about 100Å and 500Å.

10. The method according to claim 1, wherein the transparent layer of nitride UV has a thickness of less than about 500Å.

11. The method according to claim 1, wherein the transparent layer of nitride UV has a thickness of between about 100Å and 500Å.

12. The method according to claim 1, wherein the transparent layer of nitride UV has a thickness of between about 200Å and 500Å.

13. A machine-readable medium encoded with a program for contact opening definition for active element electrical connections, said program containing instructions for performing the steps of:

forming a layer of BPSG on a surface of an integrated circuit; and
forming a transparent layer of nitride UV above the layer of BPSG.

14. The machine-readable medium according to claim 13, wherein the program further contains instructions for performing the step of:

after the step of forming a transparent layer of nitride UV, forming two overlapped layers of BARC and resist on the surface of the integrated circuit.

15. The machine-readable medium according to claim 13, wherein the program further contains instructions for performing the step of:

before the step of forming a layer of BPSG, forming a USG oxide layer on the surface of the integrated circuit, the USG oxide layer having a thickness of between about 500Å and 2500Å.

16. The machine-readable medium according to claim 13, wherein in the step of forming the transparent layer of nitride UV, the transparent layer of nitride UV is formed by deposition using an HDP process.

17. The machine-readable medium according to claim 13, wherein in the step of forming the transparent layer of nitride UV, the transparent layer of nitride UV is formed by deposition using a CVD process.

18. The machine-readable medium according to claim 13, wherein the transparent layer of nitride UV has a thickness of less than about 500Å.

19. The machine-readable medium according to claim 13, wherein the transparent layer of nitride UV has a thickness of between about 100Å and 500Å.